

HiPerFET™ Power MOSFETs

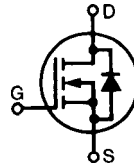
IXFK72N20
IXFK80N20

V_{DSS}	I_{D25}	$R_{DS(on)}$
200 V	72 A	35 mΩ
200 V	80 A	30 mΩ

$t_{rr} \leq 200$ ns

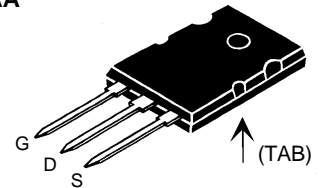
N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}

Preliminary data



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	200	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ MΩ	200	V
V_{GS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	$T_C = 25^\circ\text{C}$	72N20	72 A
		80N20	80 A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	72N20	288 A
		80N20	320 A
I_{AR}	$T_C = 25^\circ\text{C}$	74	A
E_{AR}	$T_C = 25^\circ\text{C}$	45	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/μs, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	360	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.063 in) from case for 10 s	300 -	°C
M_d	Mounting torque	0.9/6	Nm/lb.in.
Weight		10	g

TO-264 AA



G = Gate
S = Source

D = Drain
TAB = Drain

Features

- International standard packages
- Molding epoxies meet UL94 V-0 flammability classification
- Low $R_{DS(on)}$ HDMOS™ process
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

Advantages

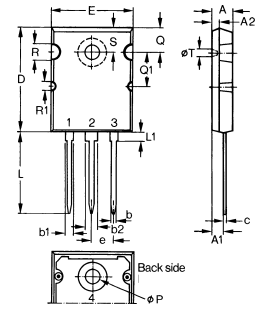
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 1$ mA	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4$ mA	2		V
I_{GSS}	$V_{GS} = \pm 20$ V _{DC} , $V_{DS} = 0$			±100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0$ V	$T_J = 25^\circ\text{C}$		200 μA
		$T_J = 125^\circ\text{C}$		1 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300$ μs, duty cycle $d \leq 2$ %	72N20		35 mΩ
		80N20		30 mΩ

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	35	42	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		5900	pF
C_{oss}			1140	pF
C_{rss}			480	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = (\text{External})$,		40	ns
t_r			55	ns
$t_{d(off)}$			120	ns
t_f			26	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		280	nC
Q_{gs}			39	nC
Q_{gd}			120	nC
R_{thJC}			0.35	K/W
R_{thCK}			0.15	K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$	72N20 80N20		72 A 80 A
I_{SM}	Repetitive; pulse width limited by T_{JM}	72N20 80N20		288 A 320 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		1.2	200 ns
Q_{RM}			10	μC
I_{RM}				A

TO-264 AA Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46	BSC	.215	BSC
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

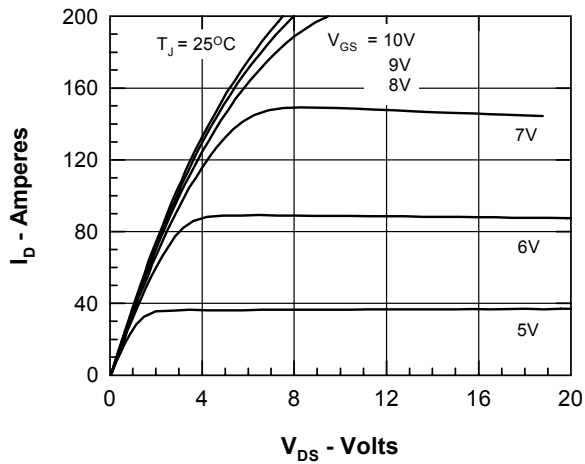


Figure 1. Output Characteristics at 25°C

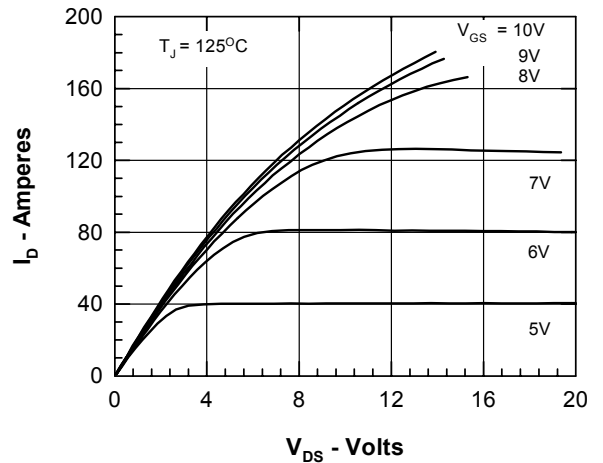


Figure 2. Output Characteristics at 125°C

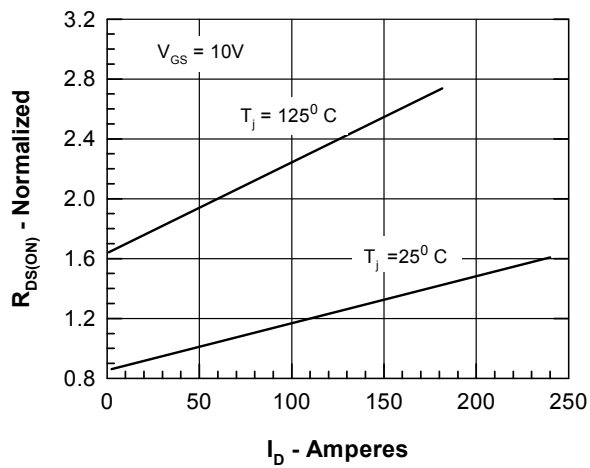


Figure 3. $R_{DS(on)}$ normalized to 0.5 I_{D25} value

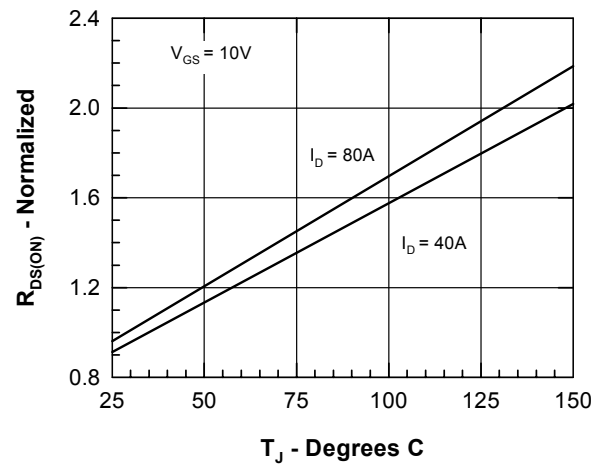


Figure 4. $R_{DS(on)}$ normalized to 0.5 I_{D25} value

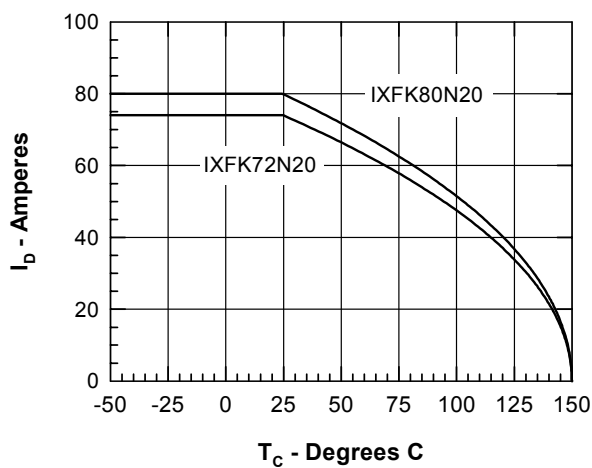


Figure 5. Drain Current vs. Case Temperature

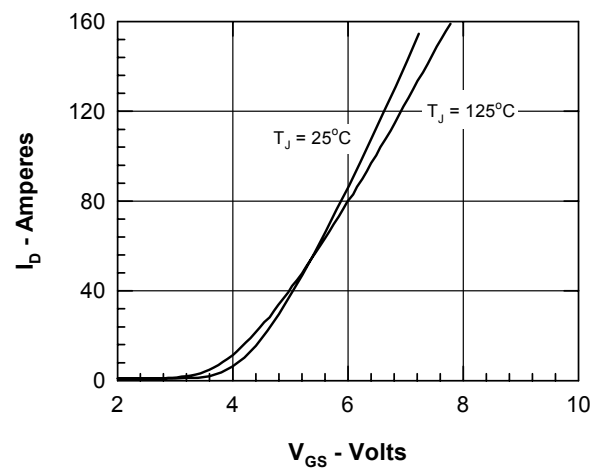


Figure 6. Admittance Curves

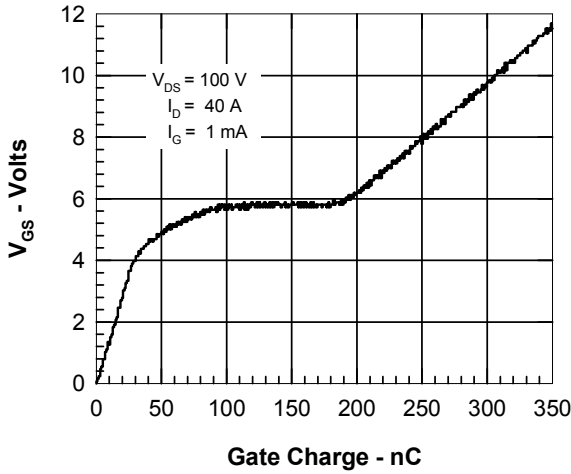


Figure 7. Gate Charge

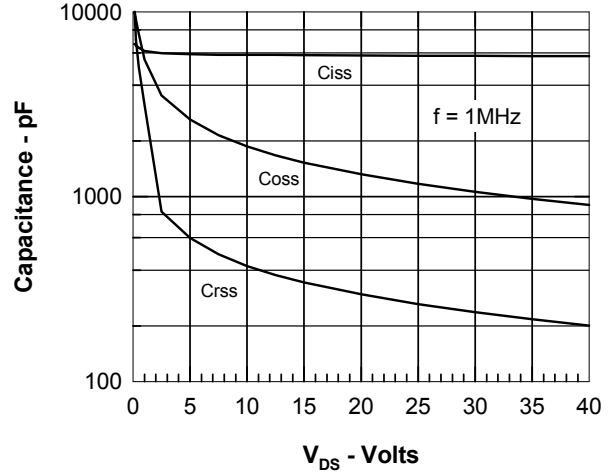


Figure 8. Capacitance Curves

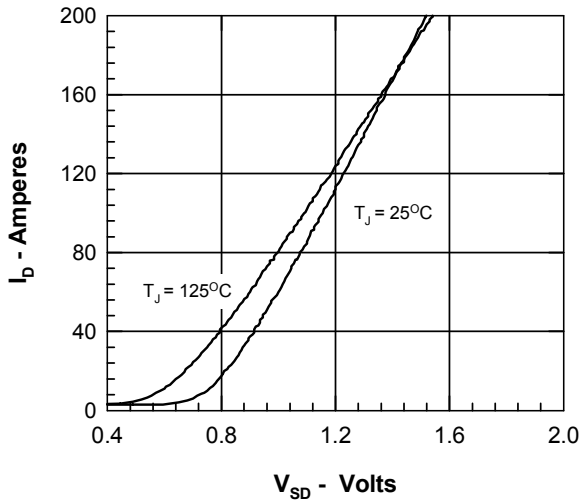


Figure 9. Source Current vs. Source to Drain Voltage

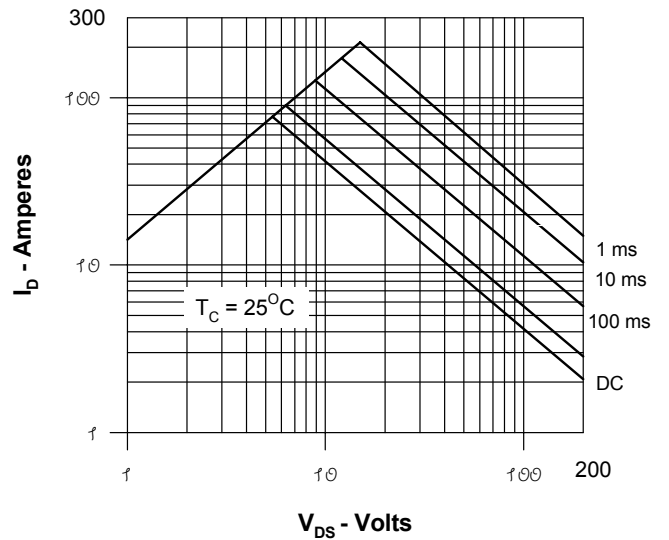


Figure 10. Forward Bias Safe Operating Area

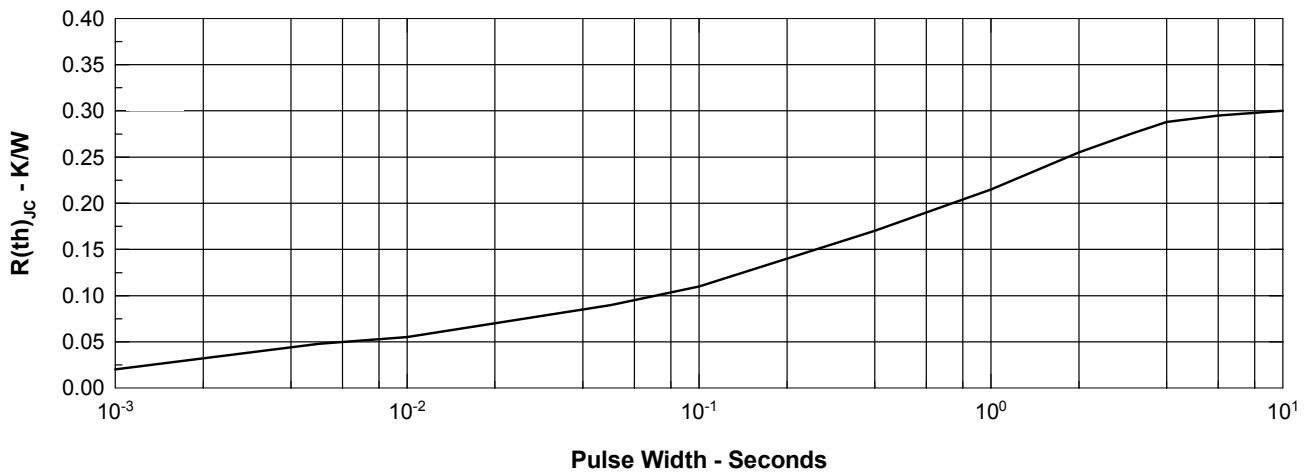


Figure 11. Transient Thermal Resistance